

## Dual N-Channel 20 V (D-S) MOSFET

### PRODUCT SUMMARY

| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (mΩ)(Typ.) | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |
|---------------------|--------------------------------|---------------------------------|-----------------------|
| 20                  | 32 at V <sub>GS</sub> = 4.5 V  | 6                               | 4.75 nC               |
|                     | 45 at V <sub>GS</sub> = 2.5 V  |                                 |                       |

### FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- Low Gate Charge

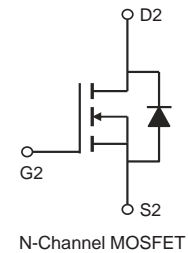
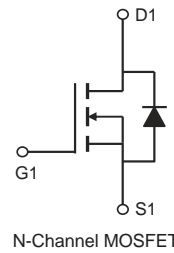
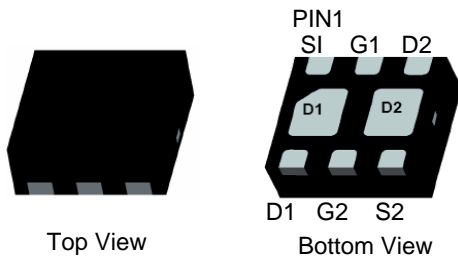
### APPLICATIONS

- Load Switch
- DC/DC Converters



**RoHS**  
COMPLIANT

DFN 2X2-6



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

| PARAMETER   | SYMBOL                            | LIMIT                   | UNIT |
|---|-----------------------------------|-------------------------|------|
| Drain-Source Voltage  | V <sub>DS</sub>                   | 20                      | V    |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ± 12                    |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | I <sub>D</sub>                    | T <sub>A</sub> = 25 °C  | 6    |
|   |                                   | T <sub>A</sub> = 100 °C | 4.2  |
| Pulsed Drain Current <sup>b</sup>                               | I <sub>DM</sub>                   | 24                      | A    |
| Maximum Power Dissipation <sup>c</sup>                          | P <sub>D</sub>                    | T <sub>A</sub> = 25 °C  | 2.4  |
|   |                                   | T <sub>A</sub> = 100 °C | 0.96 |
| Operating Junction and Storage Temperature Range                | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150             | °C   |

### THERMAL RESISTANCE RATINGS

| PARAMETER                                    | SYMBOL            | LIMIT | UNIT |
|--|-------------------|-------|------|
| Junction-to-Ambient (PCB Mount) <sup>d</sup> | R <sub>thJA</sub> | 52    | °C/W |

#### Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P<sub>D</sub> is based on max. junction temperature, using junction-ambient thermal resistance.
- The value of R<sub>thJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.

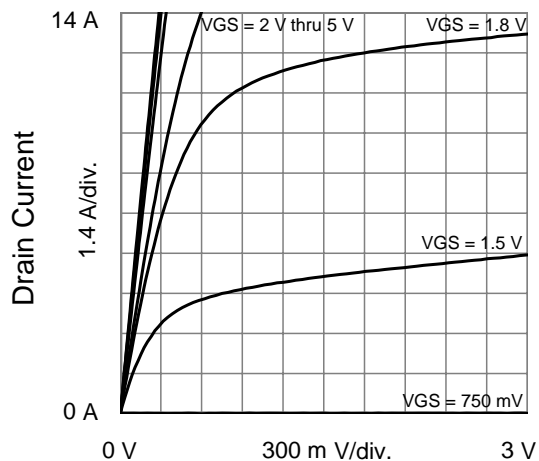
| SPECIFICATIONS (T <sub>A</sub> = 25 °C, unless otherwise noted)                                |                     |   |      |      |       |      |
|--|---------------------|---|------|------|-------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | MIN. | TYP. | MAX.  | UNIT |
| <b>Static</b>  |                     |   |      |      |       |      |
| Drain-Source Breakdown Voltage   | V <sub>DS</sub>     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA  | 20   | -    | -     | V    |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                   | 0.4  | -    | 1.2   |      |
| Gate-Body Leakage  | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V   | -    | -    | ± 100 | nA   |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V   | -    | -    | 1     | μA   |
|  |                     | V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                         | -    | -    | 100   |      |
| On-State Drain Current <sup>a</sup>  | I <sub>D(on)</sub>  | V <sub>DS</sub> ≤ 5 V, V <sub>GS</sub> = 5 V  | 6    | -    | -     | A    |
| Drain-Source On-State Resistance <sup>a</sup>  | R <sub>DS(on)</sub> | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A   | -    | 32   | 40    | mΩ   |
|  |                     | V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 5 A   | -    | 45   | 55    |      |
| Forward Transconductance <sup>a</sup>  | g <sub>fs</sub>     | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 5 A   | -    | 12   | -     | S    |
| <b>Dynamic<sup>b</sup></b>   |                     |   |      |      |       |      |
| Input Capacitance  | C <sub>iss</sub>    | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 10 V, f = 1 MHz                                      | -    | 345  | -     | pF   |
| Output Capacitance   | C <sub>oss</sub>    |   | -    | 60   | -     |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |   | -    | 52   | -     |      |
| Total Gate Charge <sup>c</sup>   | Q <sub>g</sub>      | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A                         | -    | 4.75 | -     | nC   |
| Gate-Source Charge <sup>c</sup>  | Q <sub>gs</sub>     |   | -    | 0.33 | -     |      |
| Gate-Drain Charge <sup>c</sup>   | Q <sub>gd</sub>     |   | -    | 1.3  | -     |      |
| Gate Resistance  | R <sub>g</sub>      | f = 1 MHz   | -    | 3.3  | -     | Ω    |
| Turn-On Delay Time <sup>c</sup>  | t <sub>d(on)</sub>  | V <sub>DD</sub> = 10 V, I <sub>D</sub> = 5 A, R <sub>g</sub> = 4 Ω<br>V <sub>GS</sub> = 4.5 V | -    | 5    | -     | ns   |
| Rise Time <sup>c</sup>   | t <sub>r</sub>      |   | -    | 3.5  | -     |      |
| Turn-Off Delay Time <sup>c</sup>   | t <sub>d(off)</sub> |   | -    | 16   | -     |      |
| Fall Time <sup>c</sup>   | t <sub>f</sub>      |   | -    | 4    | -     |      |
| <b>Drain-Source Body Diode Ratings and Characteristics<sup>b</sup> (T<sub>A</sub> = 25 °C)</b> |                     |   |      |      |       |      |
| Continuous Source-Drain Diode Current  | I <sub>S</sub>      | T <sub>A</sub> = 25 °C  | -    | -    | 6     | A    |
| Pulsed Current   | I <sub>SM</sub>     |   | -    | -    | 24    | A    |
| Forward Voltage <sup>a</sup>   | V <sub>SD</sub>     | I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V   | -    | -    | 1.2   | V    |
| Reverse Recovery Time  | t <sub>rr</sub>     | I <sub>F</sub> = 5 A, di/dt = 100 A/μs  | -    | 6.5  | -     | ns   |
| Reverse Recovery Charge  | Q <sub>rr</sub>     |   | -    | 1    | -     | nC   |

**Notes**

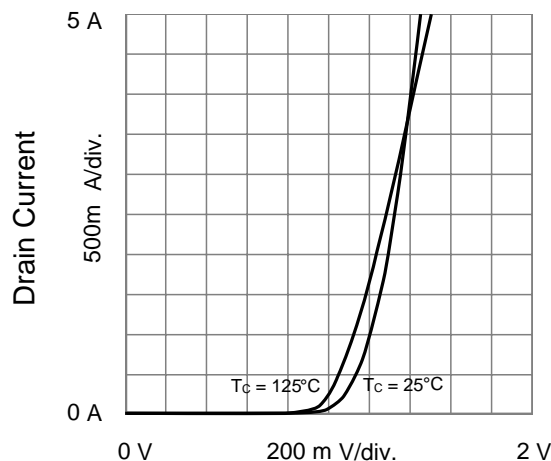
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

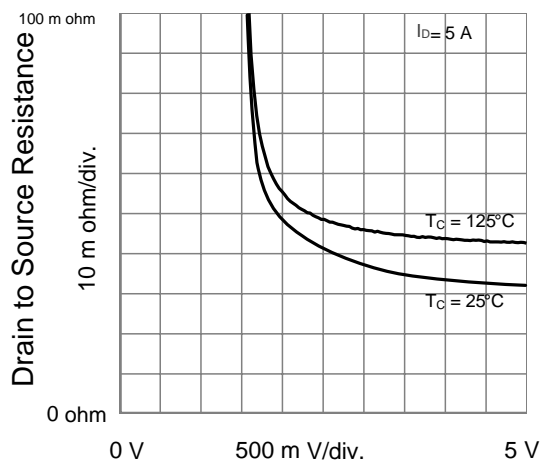
**TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**



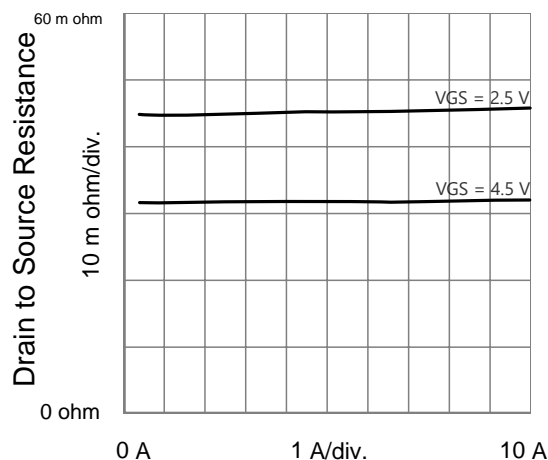
**Drain to Source Voltage Output Characteristics**



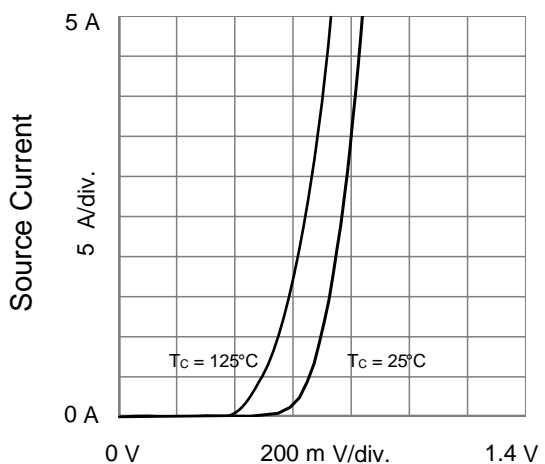
**Gate to Source Voltage Transfer Characteristics**



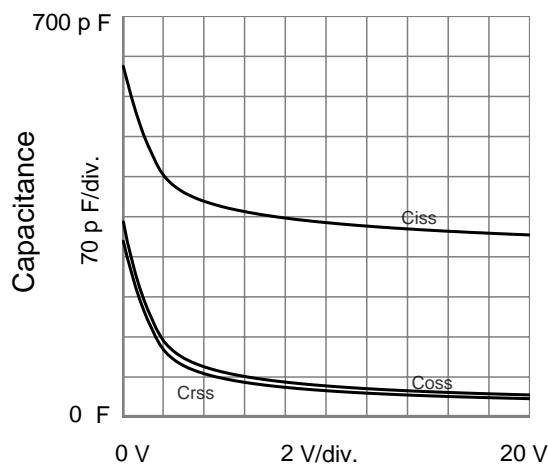
**Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage**



**Drain Current**

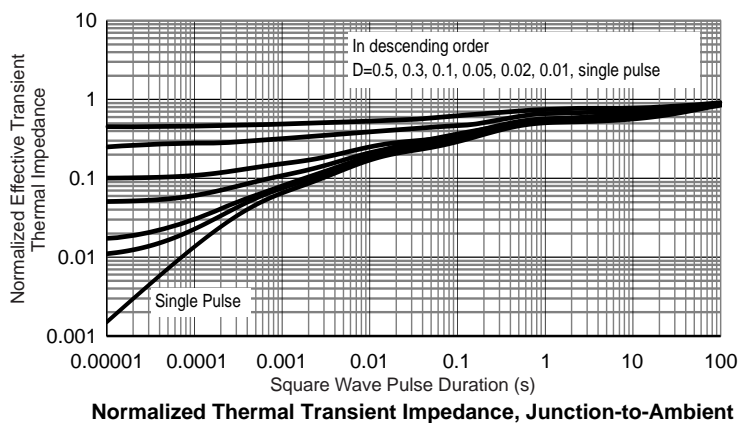
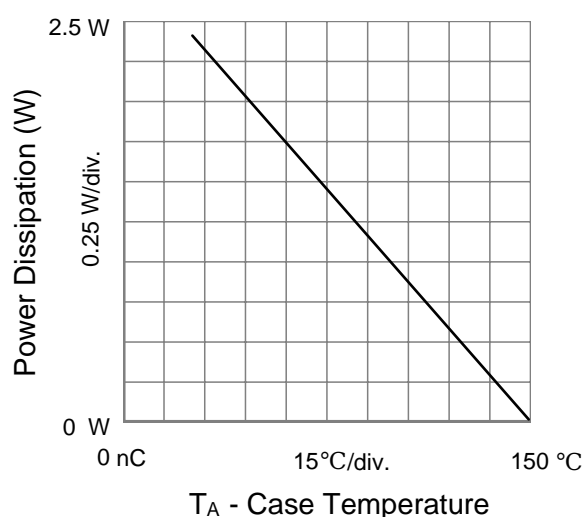
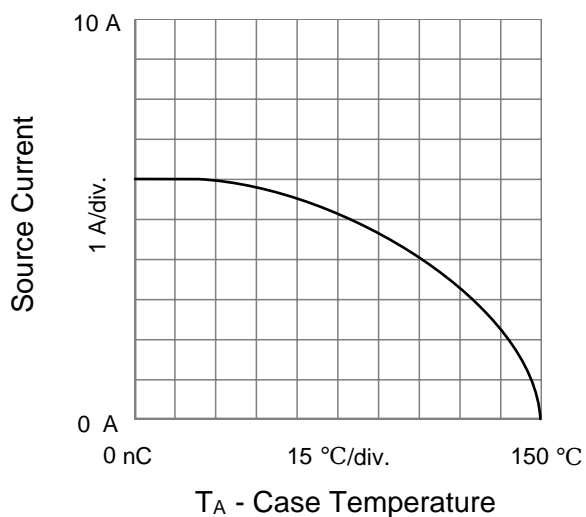
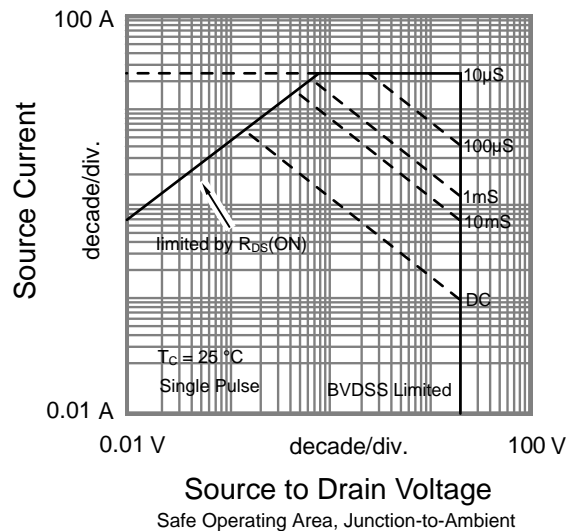
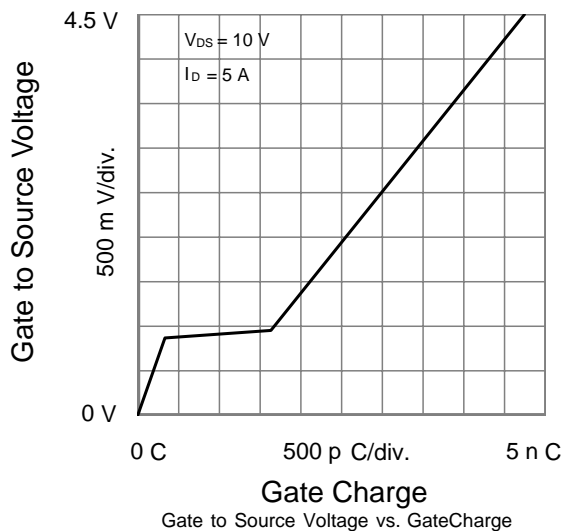


**Source to Drain Voltage Body Diode Forward Characteristics**

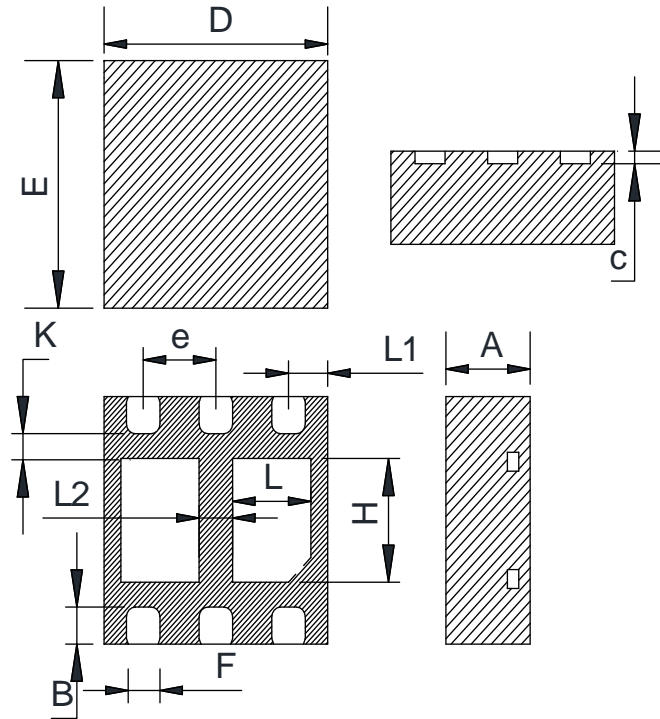


**Drain to Source Voltage Capacitances**

**TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)**



**DFN 2X2-D PACKAGE OUTLINE**



**COMMON DIMENSIONS**  
(UNITS OF MEASURE=MILLIMETER)

| Symbol | Min   | Typ   | Max   |
|--------|-------|-------|-------|
| A      | 0.70  | 0.75  | 0.80  |
| B      | 0.20  | 0.30  | 0.40  |
| C      | 0.153 | 0.203 | 0.253 |
| D      | 1.90  | 2.00  | 2.10  |
| E      | 1.90  | 2.00  | 2.10  |
| e      | 0.55  | 0.65  | 0.70  |
| F      | 0.20  | 0.30  | 0.40  |
| H      | 0.85  | 1.00  | 1.10  |
| L      | 0.55  | 0.70  | 0.80  |
| L1     | 0.25  | 0.35  | 0.45  |
| L2     | 0.20  | 0.30  | 0.40  |
| K      | 0.15  | 0.20  | 0.30  |

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